

### N-channel TrenchMOS standard level FET

Rev. 03 — 18 February 2011

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance

### **1.3 Applications**

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching

### 1.4 Quick reference data

#### Table 1. Quick reference data

|                      | Guick reference ua                                 |  |     |     |      |      |
|----------------------|--|--|-----|-----|------|------|
| Symbol               | Parameter  | Conditions   | Min | Тур | Max  | Unit |
| $V_{DS}$             | drain-source<br>voltage                            | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  | -   | -   | 75   | V    |
| I <sub>D</sub>       | drain current                                      | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C;<br>see <u>Figure 1</u> ; see <u>Figure 3</u>  | -   | -   | 75   | A    |
| P <sub>tot</sub>     | total power<br>dissipation                         | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   | -   | -   | 230  | W    |
| Static cha           | racteristics                                       |  |     |     |      |      |
| R <sub>DSon</sub>    | drain-source<br>on-state<br>resistance             | $\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 175 \ ^{\circ}\text{C}; \text{ see } \underline{\text{Figure 11}}; \\ \text{see } \underline{\text{Figure 12}} \end{array}$ | -   | -   | 18.9 | mΩ   |
|                      |  | $\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \ ^{\circ}\text{C}; \text{ see } \overline{\text{Figure 11}}; \\ \text{see } \overline{\text{Figure 12}} \end{array}$    | -   | 7.7 | 9    | mΩ   |
| Avalanche            | e ruggedness                                       |  |     |     |      |      |
| E <sub>DS(AL)S</sub> | non-repetitive<br>drain-source<br>avalanche energy | $ \begin{split} I_D &= 75 \text{ A};  V_{sup} \leq 75 \text{ V}; \\ R_{GS} &= 50  \Omega;  V_{GS} = 10  \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C};  \text{unclamped} \end{split} $                                      | -   | -   | 560  | mJ   |

### Suitable for standard level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

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### 2. Pinning information

| Table 2. | Pinning | information                       |                    |                |
|----------|---------|-----------------------------------|--------------------|----------------|
| Pin      | Symbol  | Description                       | Simplified outline | Graphic symbol |
| 1        | G       | gate                              |                    | _              |
| 2        | D       | drain                             | mb                 |                |
| 3        | S       | source                            |                    |                |
| mb       | D       | mounting base; connected to drain |                    | mbb076 S       |
|          |         |                                   | SOT404 (D2PAK)     |                |

### 3. Ordering information

| Table 3. Ordering information |         |  |         |  |  |
|-------------------------------|---------|--|---------|--|--|
| Type number                   | Package |  |         |  |  |
|                               | Name    | Description  | Version |  |  |
| BUK7609-75A                   | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |  |  |

### 4. Limiting values

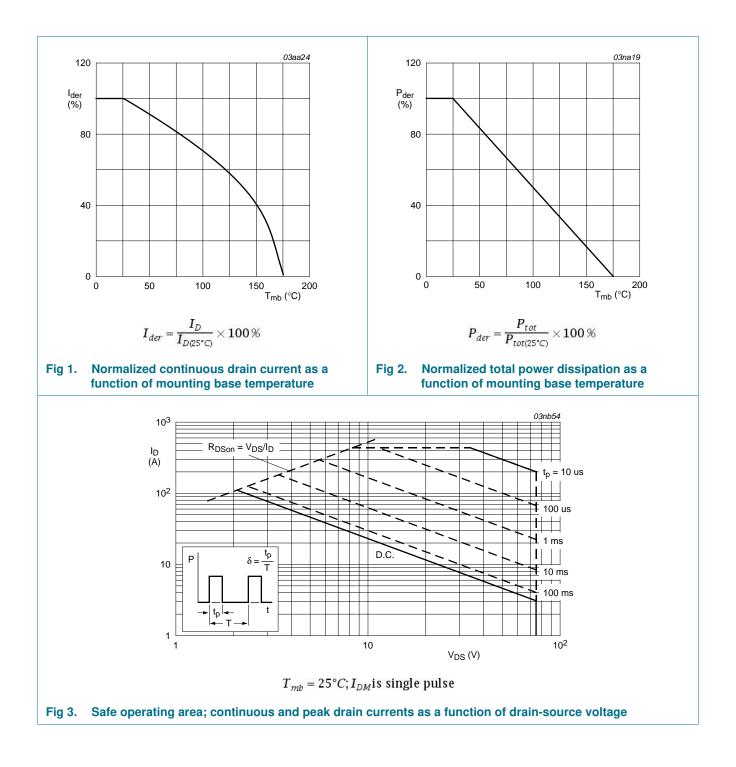
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                                       | Conditions   | Min | Max | Unit |
|------------------|---|--|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage                            | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  | -   | 75  | V    |
| V <sub>DGR</sub> | drain-gate voltage                              | $R_{GS} = 20 \text{ k}\Omega$  | -   | 75  | V    |
| V <sub>GS</sub>  | gate-source voltage                             |  | -20 | 20  | V    |
| I <sub>D</sub>   | drain current                                   | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ;<br>see <u>Figure 3</u>  | -   | 75  | А    |
|                  |   | $T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>  | -   | 65  | А    |
| I <sub>DM</sub>  | peak drain current                              | T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs;<br>see <u>Figure 3</u>  | -   | 440 | А    |
| P <sub>tot</sub> | total power dissipation                         | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   | -   | 230 | W    |
| T <sub>stg</sub> | storage temperature                             |  | -55 | 175 | °C   |
| Tj               | junction temperature                            |  | -55 | 175 | °C   |
| Source-drai      | n diode   |  |     |     |      |
| I <sub>S</sub>   | source current                                  | T <sub>mb</sub> = 25 °C  | -   | 75  | А    |
| I <sub>SM</sub>  | peak source current                             | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$   | -   | 440 | А    |
| Avalanche r      | ruggedness                                      |  |     |     |      |
| $E_{DS(AL)S}$    | non-repetitive drain-source<br>avalanche energy | $\label{eq:ID} \begin{array}{l} I_{D} = 75 \; A; \; V_{sup} \leq 75 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$ | -   | 560 | mJ   |
|                  |   |  |     |     |      |

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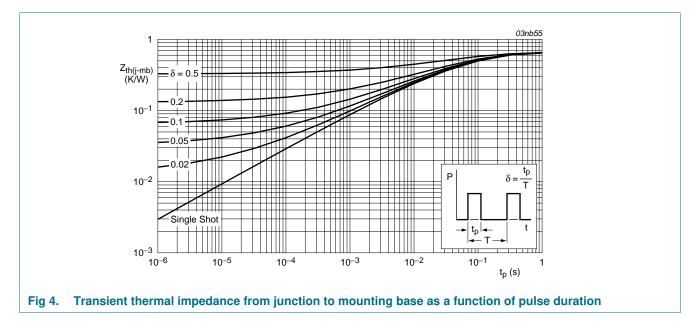
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### 5. Thermal characteristics

| Table 5.             | Thermal characteristics                           |  |     |     |      |      |
|----------------------|---|--|-----|-----|------|------|
| Symbol               | Parameter   | Conditions   | Min | Тур | Max  | Unit |
| $R_{th(j-mb)}$       | thermal resistance from junction to mounting base | see Figure 4   | -   | -   | 0.65 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient       | mounted on a printed-circuit board;<br>minimum footprint | -   | 50  | -    | K/W  |

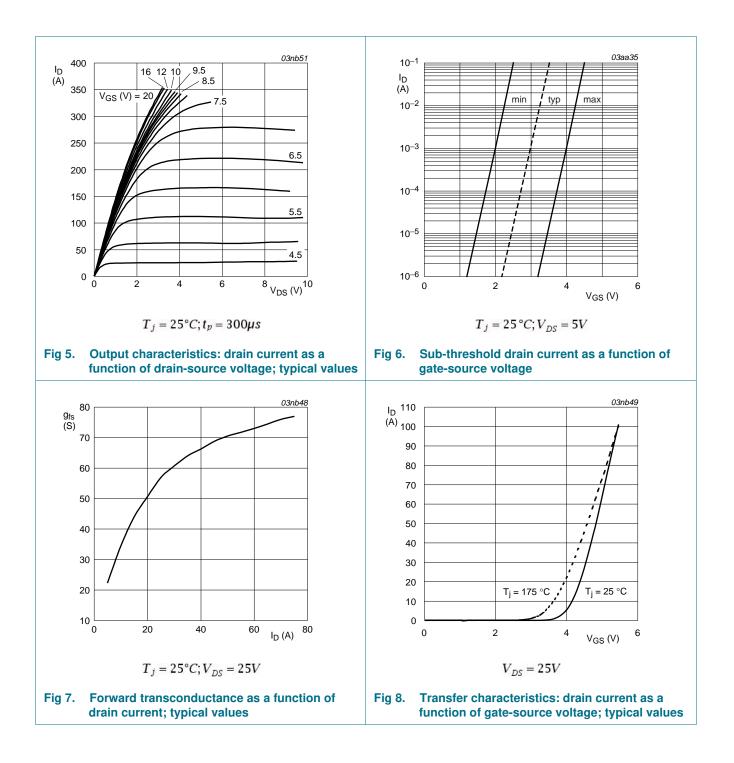


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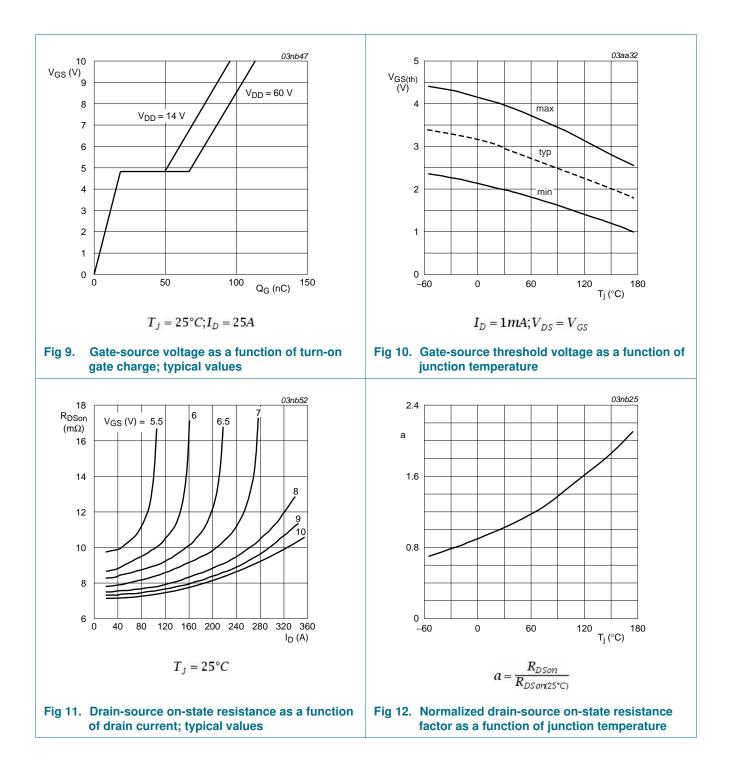
### 6. Characteristics

| Table 6.             | Characteristics                  |  |     |      |      |      |
|----------------------|----------------------------------|--|-----|------|------|------|
| Symbol               | Parameter                        | Conditions   | Min | Тур  | Max  | Unit |
| Static cha           | aracteristics                    |  |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source                     | $I_D = 0.25 \text{ mA};  V_{GS} = 0  \text{V};  \text{T}_j = \text{-}55 ^\circ\text{C}$                                | 70  | -    | -    | V    |
|                      | breakdown voltage                | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | 75  | -    | -    | V    |
| $V_{GS(th)}$         | gate-source threshold voltage    | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C;<br>see <u>Figure 10</u>            | 1   | -    | -    | V    |
|                      |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$<br>see <u>Figure 10</u>                                    | 2   | 3    | 4    | V    |
|                      |                                  | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = -55 °C;<br>see <u>Figure 10</u>            | -   | -    | 4.4  | V    |
| I <sub>DSS</sub>     | drain leakage current            | $V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$  | -   | -    | 500  | μA   |
|                      |                                  | $V_{DS} = 75 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$   | -   | 0.05 | 10   | μΑ   |
| I <sub>GSS</sub>     | gate leakage current             | $V_{GS} = 20 \text{ V};  V_{DS} = 0 \text{ V};  T_{j} = 25 ^{\circ}\text{C}$   | -   | 2    | 100  | nA   |
|                      |                                  | $V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C  | -   | 2    | 100  | nA   |
| DOON                 | drain-source on-state resistance | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C;<br>see <u>Figure 11</u> ; see <u>Figure 12</u> | -   | -    | 18.9 | mΩ   |
|                      |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C;<br>see <u>Figure 11</u> ; see <u>Figure 12</u>  | -   | 7.7  | 9    | mΩ   |
| Dynamic              | characteristics                  |  |     |      |      |      |
| C <sub>iss</sub>     | input capacitance                | $V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$  | -   | 5068 | 6760 | pF   |
| C <sub>oss</sub>     | output capacitance               | $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$   | -   | 1082 | 1300 | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance     | $V_{GS} = 0 V; V_{DS} 25 V; f = 1 MHz;$<br>T <sub>j</sub> = 25 °C; see <u>Figure 13</u>                                | -   | 620  | 850  | pF   |
| t <sub>d(on)</sub>   | turn-on delay time               | $V_{DS}$ = 30 V; $R_L$ = 1.2 $\Omega$ ; $V_{GS}$ = 10 V;   | -   | 35   | -    | ns   |
| t <sub>r</sub>       | rise time                        | $R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$   | -   | 107  | -    | ns   |
| t <sub>d(off)</sub>  | turn-off delay time              |  | -   | 183  | -    | ns   |
| t <sub>f</sub>       | fall time                        |  | -   | 100  | -    | ns   |
| L <sub>D</sub>       | internal drain<br>inductance     | from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$   | -   | 2.5  | -    | nH   |
|                      |                                  | from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$  | -   | 4.5  | -    | nH   |
| L <sub>S</sub>       | internal source<br>inductance    | from source lead to source bond pad;<br>$T_j = 25 \text{ °C}$  | -   | 7.5  | -    | nH   |
| Source-d             | rain diode                       |  |     |      |      |      |
| $V_{SD}$             | source-drain voltage             | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$<br>see Figure 14                                      | -   | 0.85 | 1.2  | V    |
| t <sub>rr</sub>      | reverse recovery time            | $I_{\rm S} = 20 \text{ A}; \text{ dI}_{\rm S}/\text{dt} = -100 \text{ A}/\mu\text{s};$                                 | -   | 75   | -    | ns   |
| Q <sub>r</sub>       | recovered charge                 | V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C  | -   | 270  | -    | nC   |

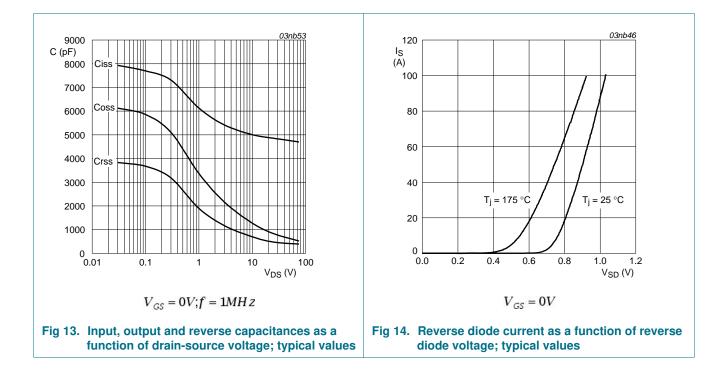
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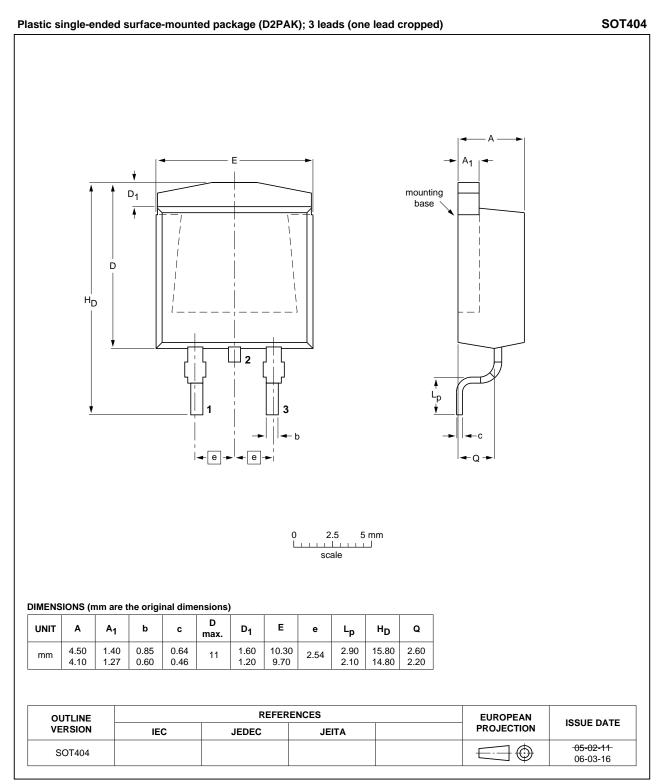


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### 7. Package outline



#### Fig 15. Package outline SOT404 (D2PAK)

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### 8. Revision history

| Table 7. Revision histo | ory   |   |                    |                      |
|-------------------------|---|---|--------------------|----------------------|
| Document ID             | Release date  | Data sheet status   | Change notice      | Supersedes           |
| BUK7609-75A v.3         | 20110218  | Product data sheet  | -                  | BUK7509_7609_75A v.2 |
| Modifications:          | guidelines of NX <ul> <li>Legal texts have</li> </ul> | nis data sheet has been re<br>XP Semiconductors.<br>e been adapted to the ne<br>UK7609-75A separated fi | w company name whe | ere appropriate.     |
| BUK7509_7609_75A v.2    | 20001106  | Product specification   | -                  | BUK7509_7609_75A v.1 |
| BUK7509_7609_75A v.1    | 20001010  | Product specification   | -                  | -                    |

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| Document status [1] [2]        | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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